

FEATURES

- High frequency operation
- High surge forward current capability
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

TYPICAL APPLICATIONS

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MECHANICAL DATA

- **Package:** TO-247AD-2L
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked

MAXIMUM RATINGS (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MUR6060P
Device marking code			MUR6060P
Repetitive Peak Reverse Voltage	VRRM	V	600
Average Rectified Output Current @60Hz half sine-wave, R-load, T _c (FIG.1)	I _o	A	60
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T _a =25°C	I _{FSM}	A	350
Current Squared Time @1ms≤t≤8.3ms T _j =25°C	I ² t	A ² s.	510
Storage Temperature	T _{stg}	°C	-55 ~ +175
Junction Temperature	T _j	°C	-55 ~ +175

ELECTRICAL CHARACTERISTICS (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MUR6060P
Maximum instantaneous forward voltage drop per diode	V _{FM}	V	I _{FM} =60.0A	1.7
Maximum DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	uA	V _{RM} =VRRM T _a =25°C	15
	I _{RRM2}		V _{RM} =VRRM T _a =125°C	500
Reverse Recovery Time	T _{rr}	ns	I _F =0.5A I _{RM} =1A I _{RR} =0.25A	75

THERMAL CHARACTERISTICS (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MUR6060P
Thermal Resistance Between junction and case	R _{θj-c}	°C/W	0.8

PACKAGING INFORMATION

PREFERRED P/N	UNIT WEIGHT(g)	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MUR6060P	Approximate 6.0	33	330	1980	Tube

CHARACTERISTICS (TYPICAL)

FIG1: I_o - T_c Curve

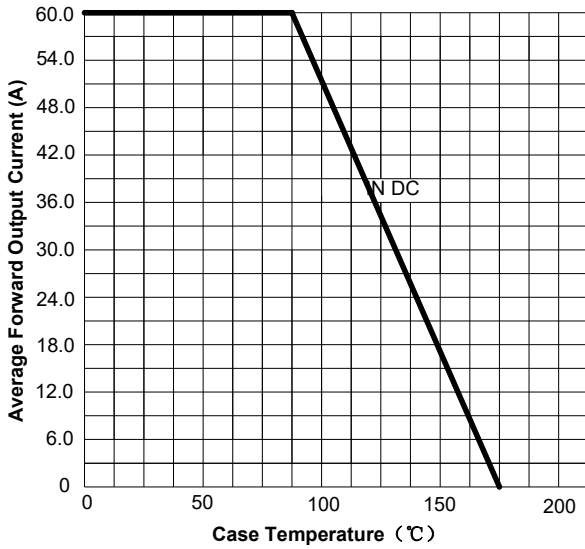


FIG2: Surge Forward Current Capability

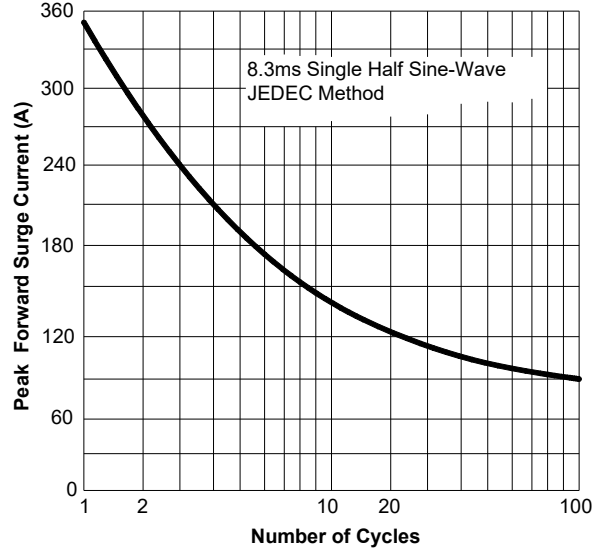


FIG3: Forward Voltage

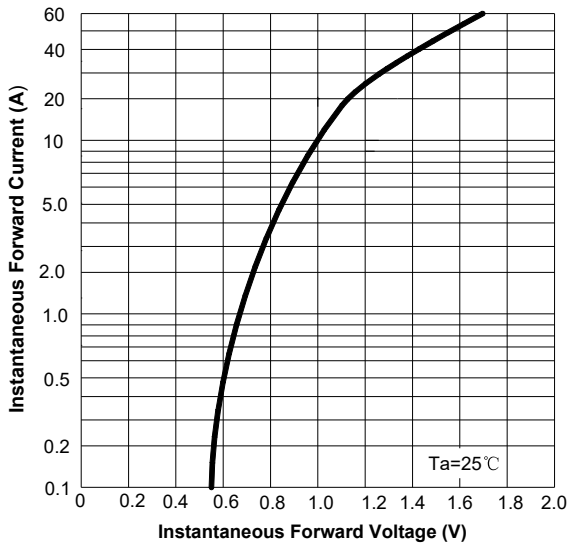


FIG4: Typical Reverse Characteristics

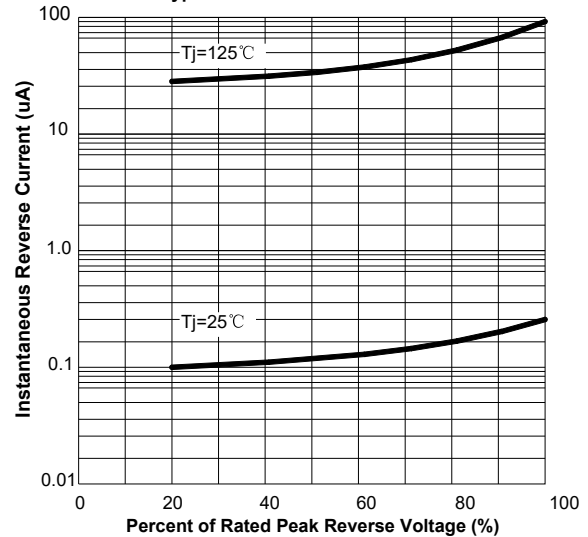
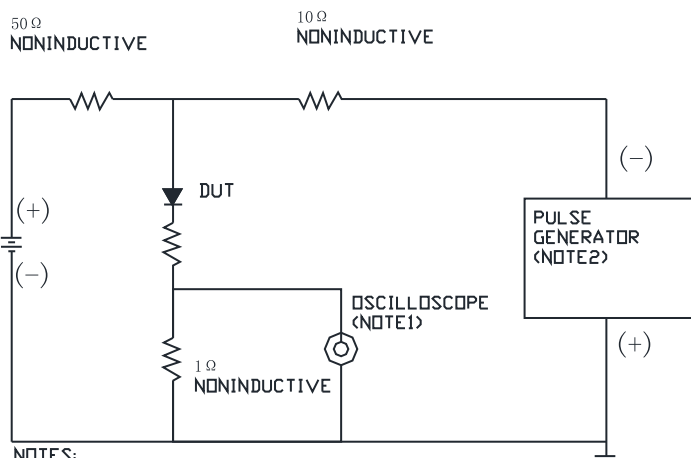
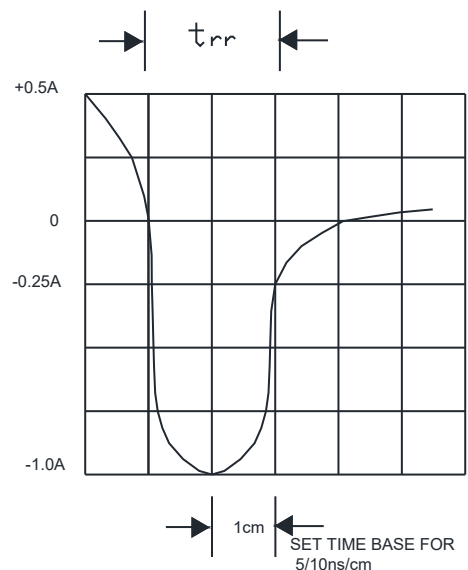


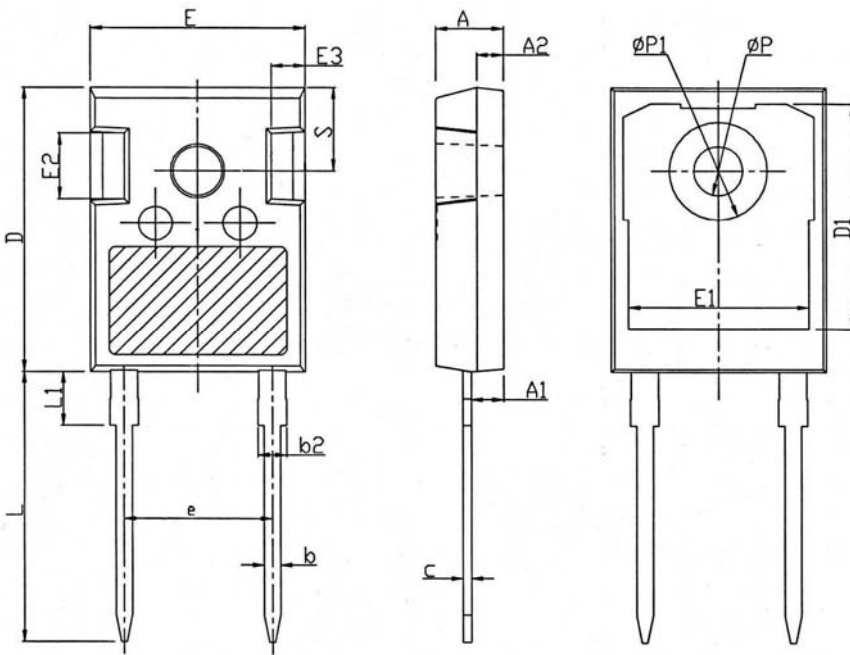
FIG.5 Diagram of circuit and Testing wave form of reverse recovery time



NOTES:
1. Rise Time = 7ns max. Input Impedance = 1MΩ 22pF
2. Rise Time = 10ns max. Source Impedance = 50Ω



■ OUTLINE DIMENSIONS



TO-247-2L		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.11	1.36
b2	1.91	2.21
c	0.51	0.75
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.00	13.60
E2	4.80	5.20
E3	2.30	2.70
e	10.88BSC	
L	19.62	20.22
L1	-	4.30
φP	3.40	3.80
φP1	-	7.30
S	6.15BSC	